

60V Dual P-Channel MOSFETs

General Description

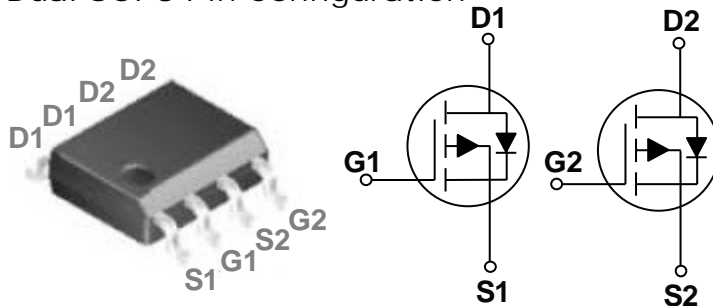
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDS(ON)	ID
-60V	105mΩ	-4A

Features

- -60V,-4A, $R_{DS(ON)} = 105m\Omega$ @ $V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Dual SOP8 Pin Configuration



Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _A =25°C)	-4	A
	Drain Current – Continuous (T _A =75°C)	-3.1	A
I _{DM}	Drain Current – Pulsed ¹	-8	A
P _D	Power Dissipation (T _A =25°C)	3.2	W
	Power Dissipation – Derate above 25°C	0.026	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	60	°C/W



FTK6809

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.05	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-60V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-48V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-2A$	---	87	105	m Ω
		$V_{GS}=-4.5V, I_D=-1A$	---	120	145	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.5	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	$\text{mV}/^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-1A$	---	3	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2, 3}	$V_{DS}=-30V, V_{GS}=-10V, I_D=-2A$	---	10.4	15	nC
Q_{gs}	Gate-Source Charge ^{2, 3}		---	1.1	1.6	
Q_{gd}	Gate-Drain Charge ^{2, 3}		---	2.7	4	
$T_{d(on)}$	Turn-On Delay Time ^{2, 3}	$V_{DD}=-30V, V_{GS}=-10V, R_G=6\Omega$ $I_D=-1A$	---	8	16	ns
T_r	Rise Time ^{2, 3}		---	15.4	30	
$T_{d(off)}$	Turn-Off Delay Time ^{2, 3}		---	42.8	80	
T_f	Fall Time ^{2, 3}		---	8.4	16	
C_{iss}	Input Capacitance	$V_{DS}=-30V, V_{GS}=0V, F=1\text{MHz}$	---	785	1300	pF
C_{oss}	Output Capacitance		---	175	300	
C_{rSS}	Reverse Transfer Capacitance		---	112	220	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	27	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-4	A
I_{SM}	Pulsed Source Current ³		---	---	-8	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=-3A, di/dt=100A/\mu s$	---	52	---	ns
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	30	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

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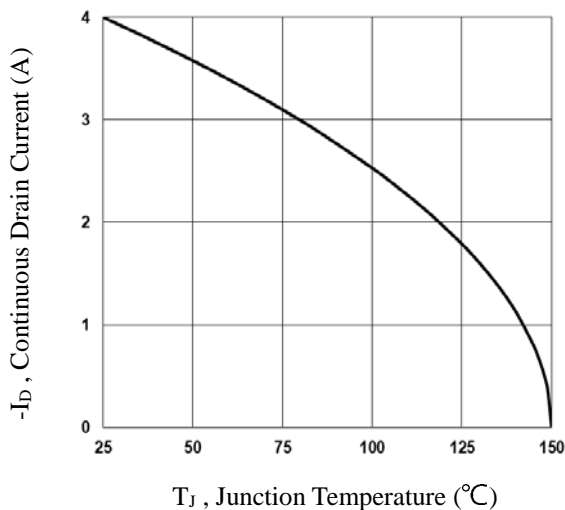


Fig.1 Continuous Drain Current vs. T_J

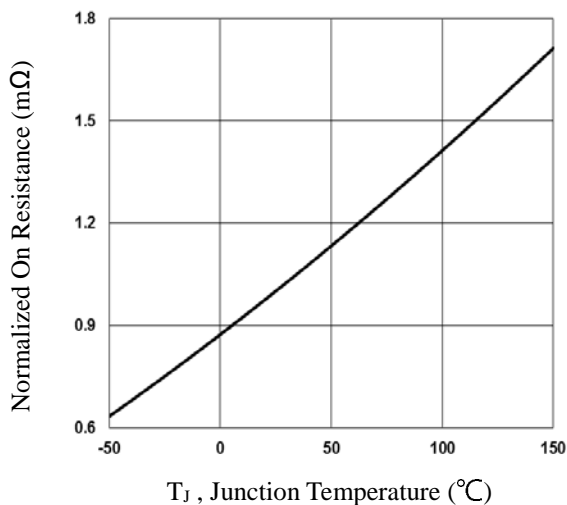


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

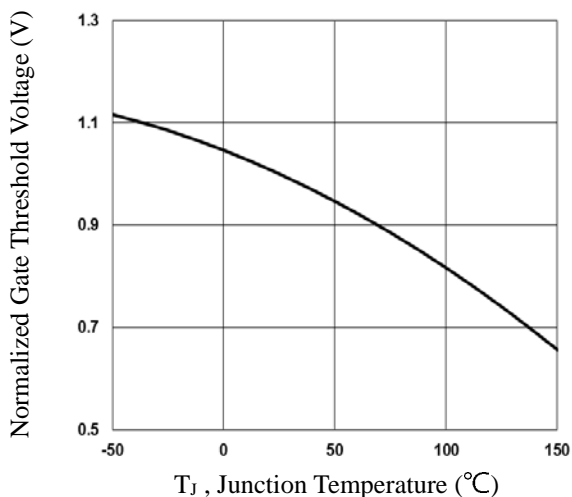


Fig.3 Normalized V_{th} vs. T_J

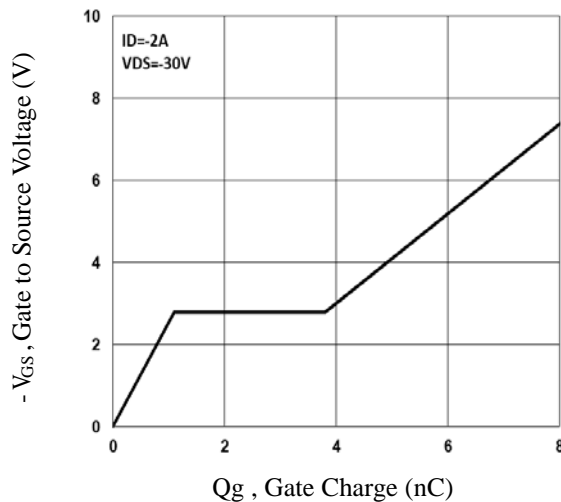


Fig.4 Gate Charge Waveform

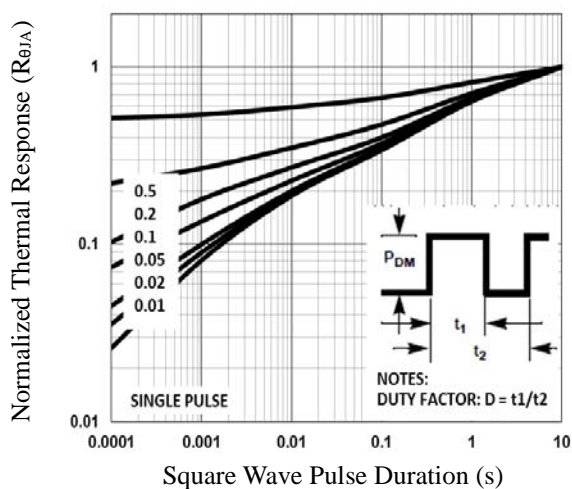


Fig.5 Normalized Transient Response

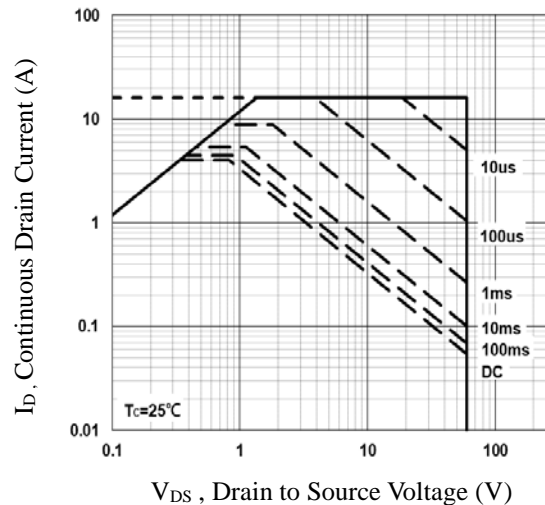


Fig.6 Maximum Safe Operation Area

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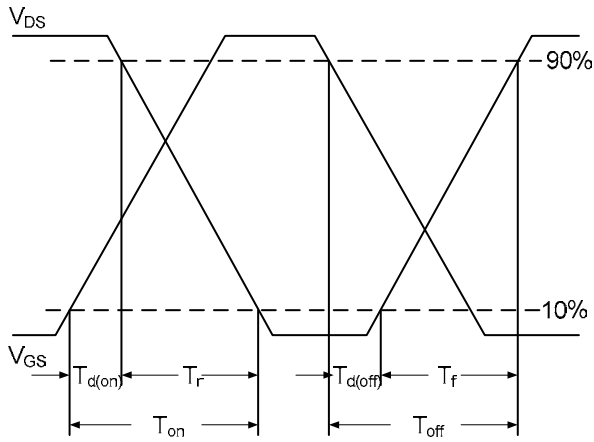


Fig.7 Switching Time Waveform

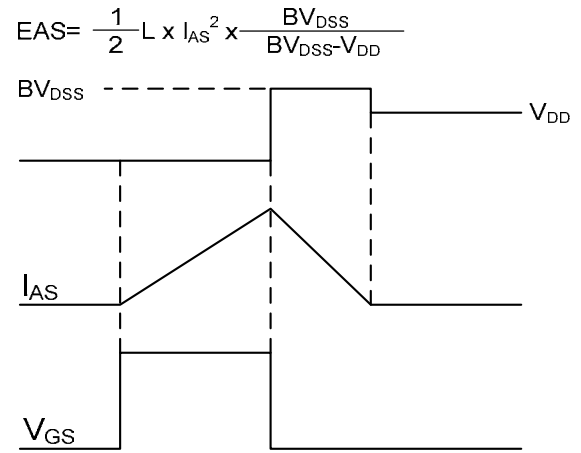
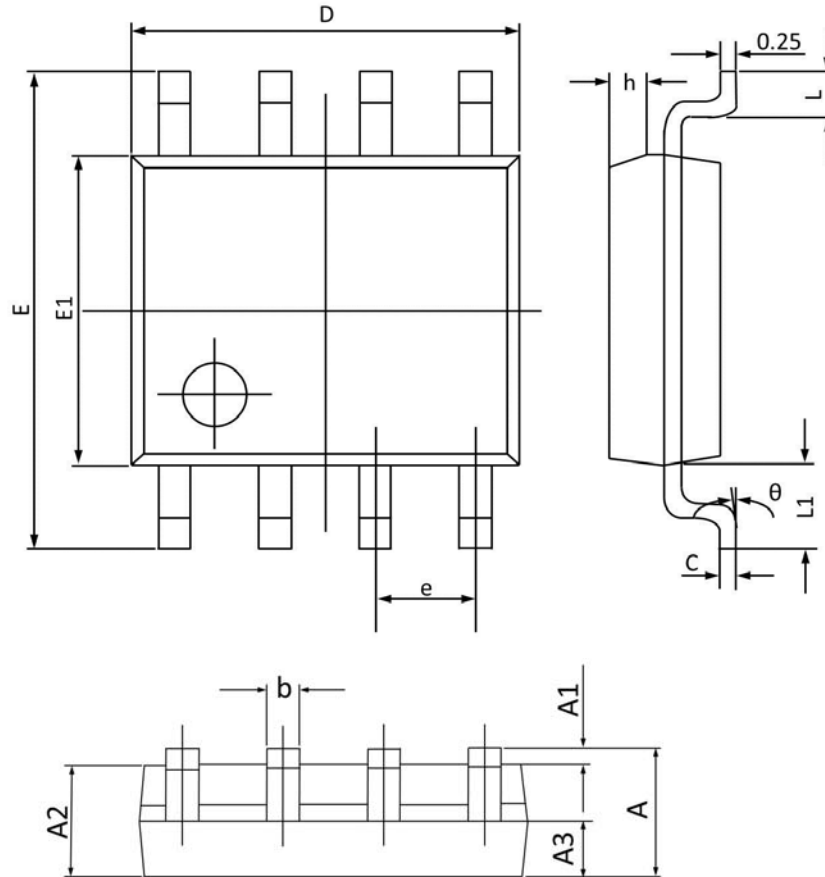


Fig.8 EAS Waveform

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SOP-8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.250	1.650	0.049	0.065
A3	0.500	0.700	0.020	0.028
b	0.380	0.510	0.015	0.020
c	0.170	0.260	0.007	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.019
L	0.400	0.800	0.019	0.031
L1	1.050(BSC)		0.041(BSC)	
theta	0°	8°	0°	8°